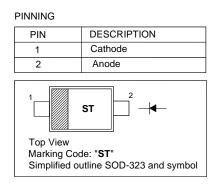
# SILICON EPITAXIAL SCHOTTKY BARRIER DIODE

### Applications

• UHF Band Mixer



### Absolute Maximum Ratings (T<sub>a</sub> = 25 °C)

5 ( 1 )			
Parameter	Symbol	Value	Unit
Peak Reverse Voltage	V <sub>RM</sub>	5	V
Forward Current	I <sub>F</sub>	30	mA
Junction Temperature	TJ	125	°C
Storage Temperature Range	T <sub>stg</sub>	- 55 to + 125	°C

#### Electrical Characteristics at T<sub>a</sub> = 25 °C

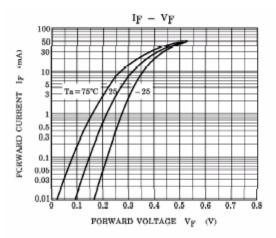
Parameter	Symbol	Min.	Тур.	Max.	Unit
Forward Current at $V_F = 0.5 V$	I <sub>F</sub>	30	-	-	mA
Reverse Current at $V_R = 0.5 V$	I <sub>R</sub>	-	-	25	μA
Total Capacitance at $V_R = 0.2 V$ , f = 1 MHz	CT	-	0.6	-	pF

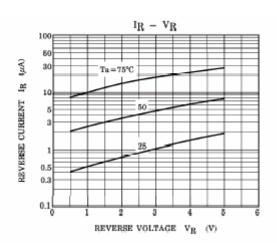


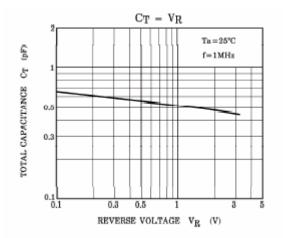




Dated : 01/09/2006











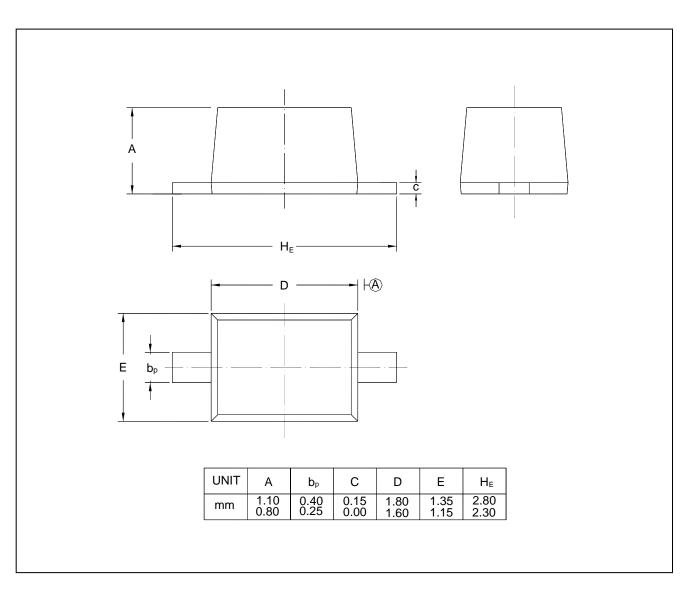


Dated : 01/09/2006

# PACKAGE OUTLINE

## Plastic surface mounted package; 2 leads

SOD-323





SEMTECH ELECTRONICS LTD. (Subsidiary of Sino-Tech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



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